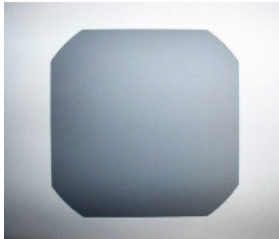


156mm x 156mm Monocrystalline Silicon Wafers CZ-Si Wafer Specifications

Technical Specifications

PV-W156MOM	
	
Crystal Type:	monocrystalline
Growth Method:	CZ
Ingot diameter	195 ± 0,5mm, / 200 ± 0,5mm
Type	Dopant P / Boron
Orientation	<100> ± 2.5°
Resitivity:	0.5 – 3 Ohm*cm or 3-6 Ohm/cm
Carbon:	< 8.0 x 10 ¹⁶ cm ⁻³
Oxygen:	< 1.0 x 10 ¹⁸ cm ⁻³
Lifetime:	> 10 μs
<p>The Sustainable Way of Life</p> <h3>Parameters of Wafers</h3>	
Wafer Square side:	156x156 ± 0,5mm
Side orientation	90° ± 0.2°
Straight sections length deviation:	< 0,5 mm
Corner between pseudosquare's side:	(90+/- 0,3) degree
Thickness of wafer	200 ± 30 μm or 240 ± 30 μm
TTV:	< 50 μm
BOW:	< 70 μm
Edge chips	not allowed